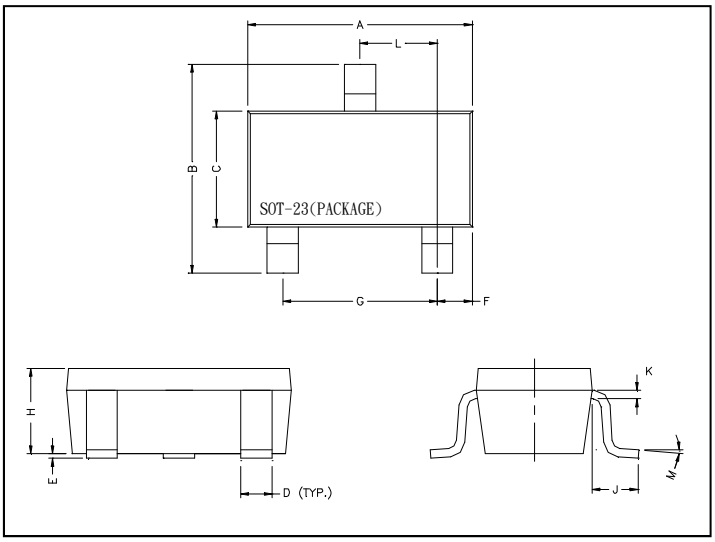
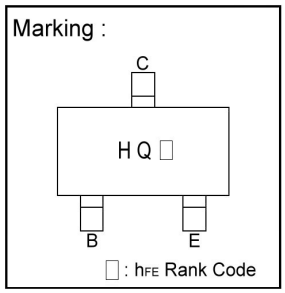
GMBT2714 NPN EPITAXIAL PLANAR TRANSISTOR

Description
The GMBT2714 is designed for use in FM, RF, MIX and IF amplifier application.

Features
- High frequency
- Very low capacitance

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	VCBO	40	V
Collector to Emitter Voltage	VCEO	30	V
Emitter to Base Voltage	VEBO	4	V
Collector Current	IC	20	mA
Total Power Dissipation	PD	225	mW

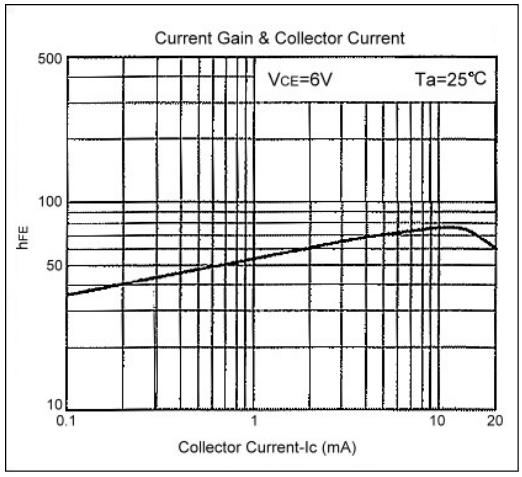
Electrical Characteristics (Ta = 25℃, unless otherwise noted)

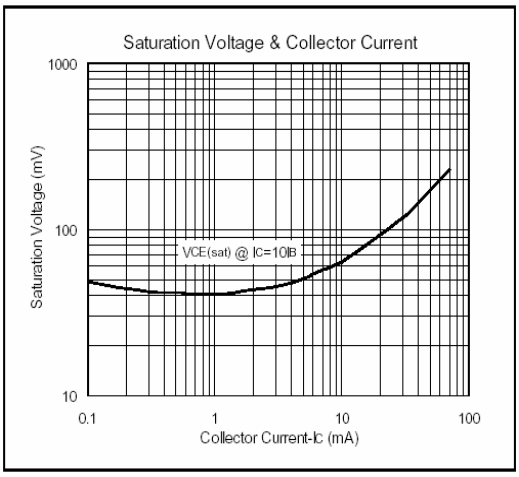
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	40	-	-	V	I_C=100uA, I_E=0
BV_{CEO}	30	-	-	V	I_C=1mA, I_B=0
BV_{EBO}	4	-	-	V	I_E=10uA, I_C=0
I_{CBO}	-	-	500	nA	V_{CB}=18V, I_E=0
I_{EBO}	-	-	500	nA	V_{EB}=4V, I_C=0
$V_{CE(sat)}$	-	-	500	mV	I_C=4mA, I_B=0.4mA
$V_{BE(on)}$	-	-	950	mV	V_{CE}=10V, I_C=4mA
h_{FE}	40	-	200		V_{CE}=6V, I_C=1mA
fT	650	-	-	MHz	V_{CE}=10V, I_C=4mA, f=100MHz
Cob	-	0.8	-	pF	V_{CB}=10V, f=1MHz

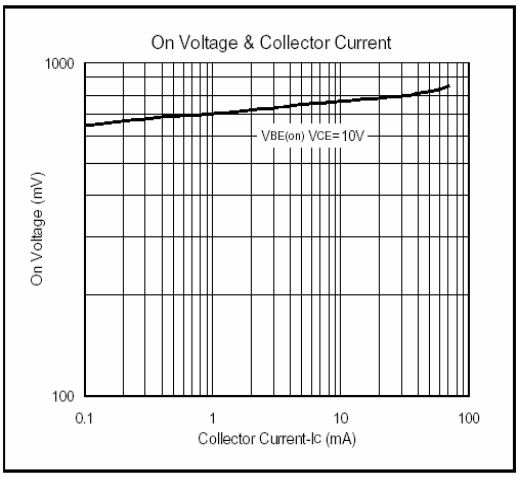
Classification Of h_{FE}

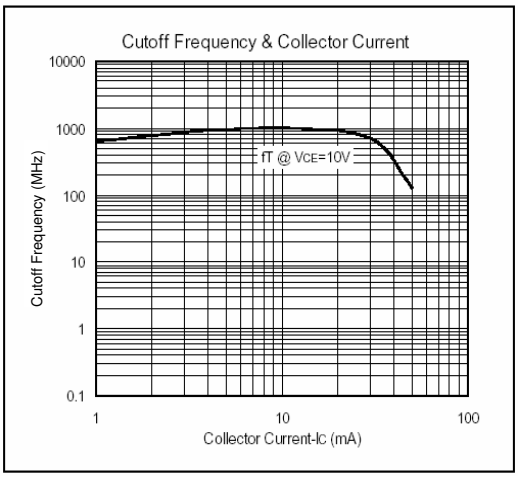
Rank	R	O	Y
Range	40 ~ 80	70 ~ 140	100 ~ 200

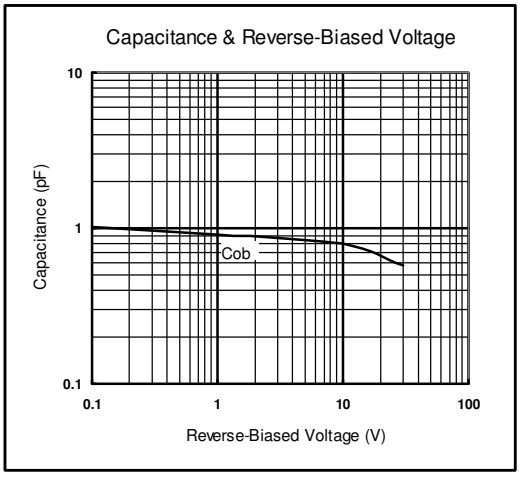
Characteristics Curve











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